

Fig. 1
PRIOR ART

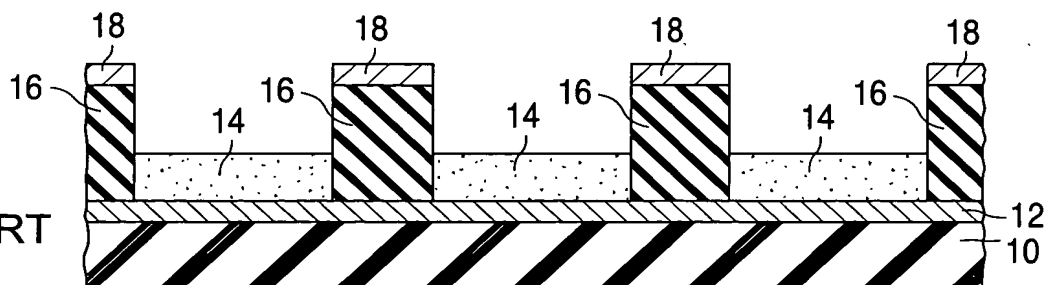


Fig. 2
PRIOR ART

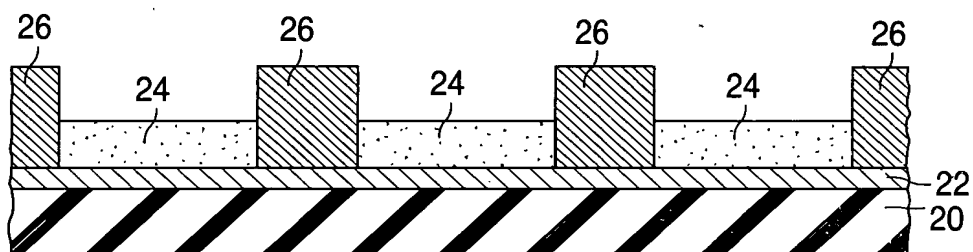


Fig. 3
PRIOR ART

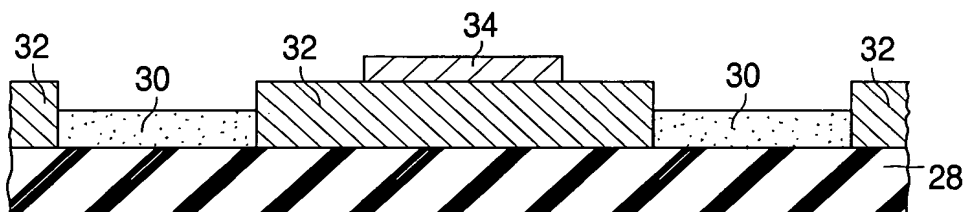
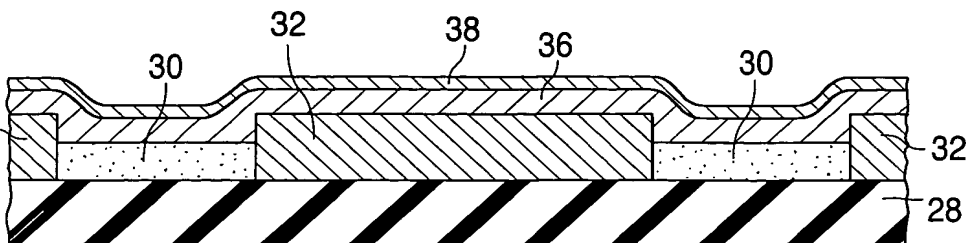


Fig. 4
PRIOR ART



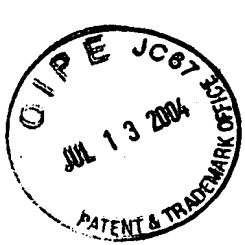
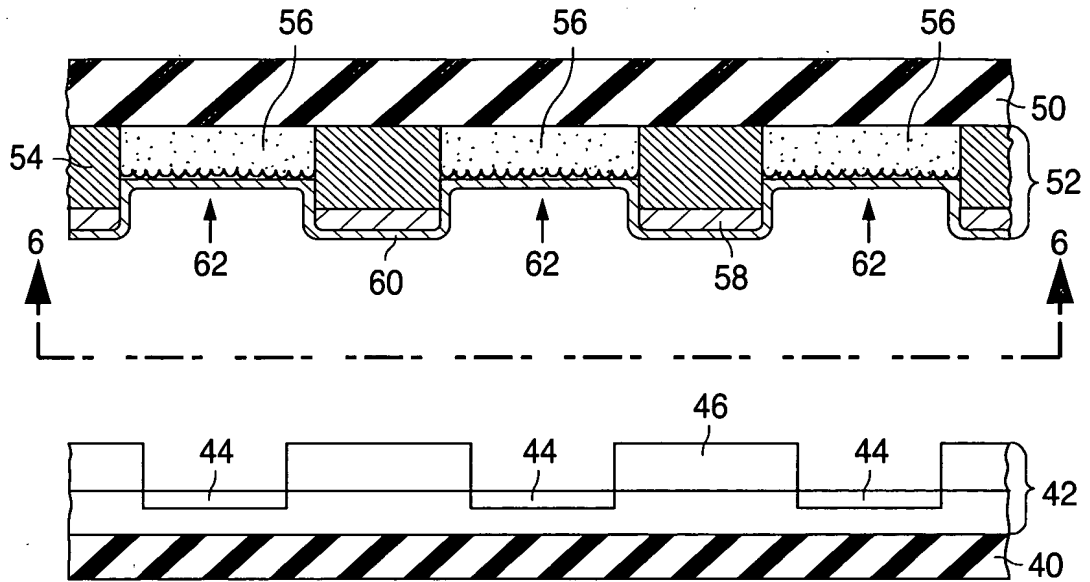
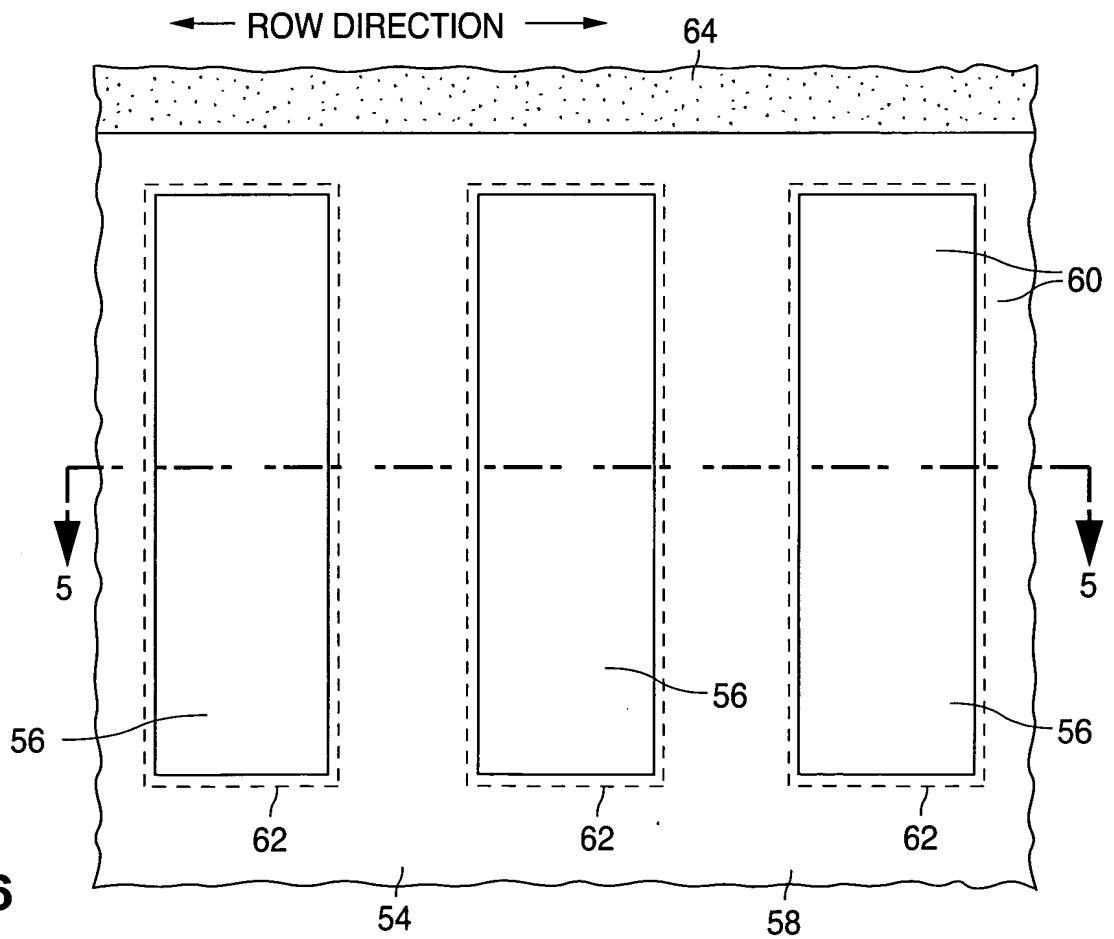


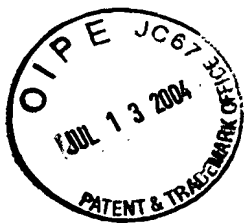
Fig. 5



COLUMN DIRECTION

Fig. 6





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Fig. 7

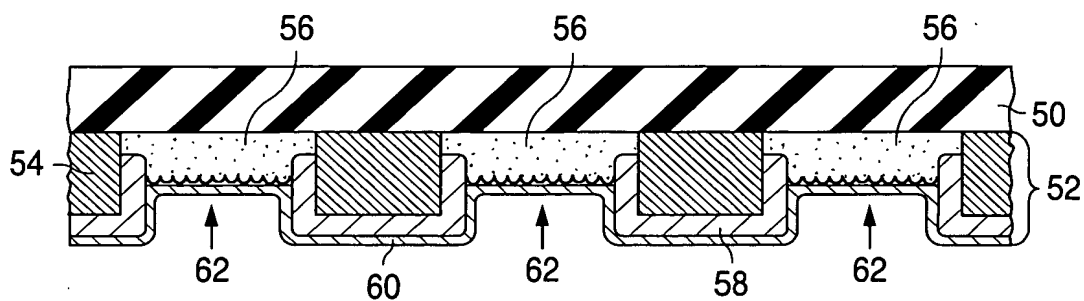


Fig. 8

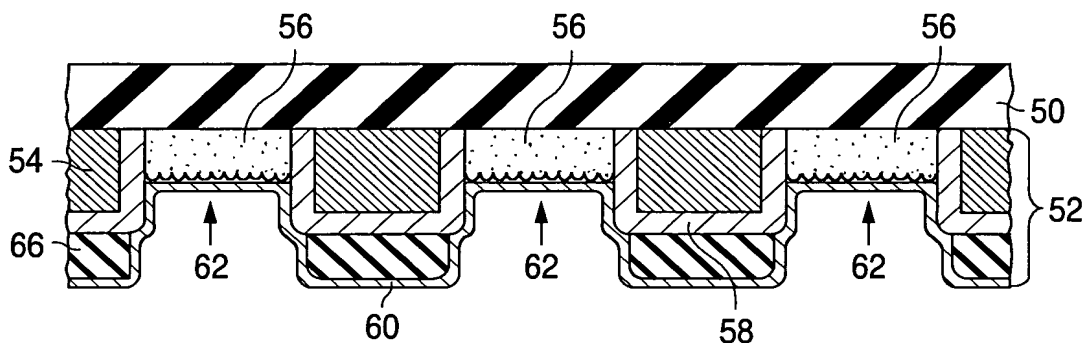
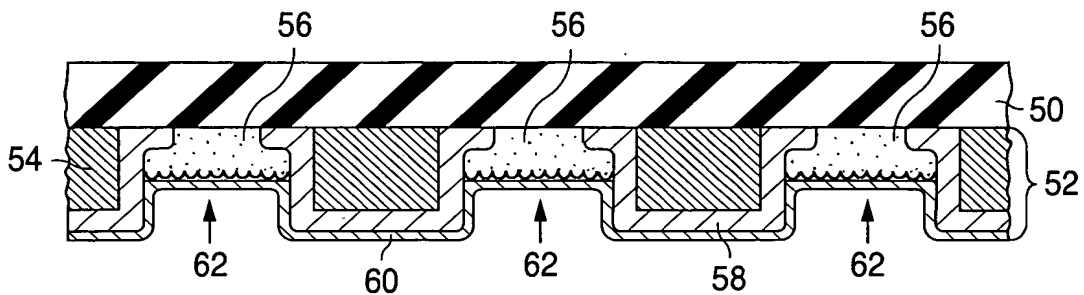
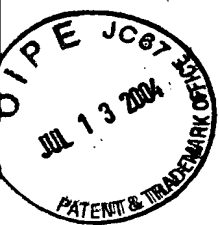
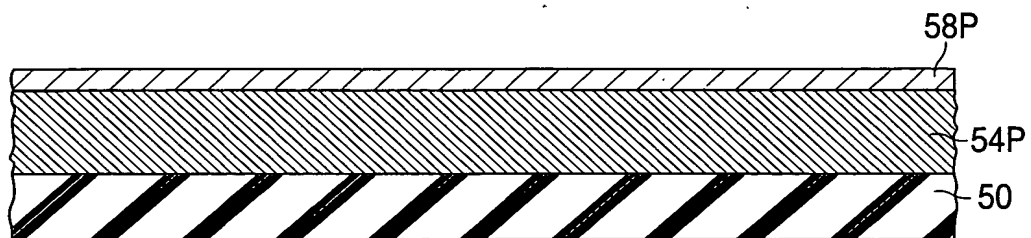


Fig. 9

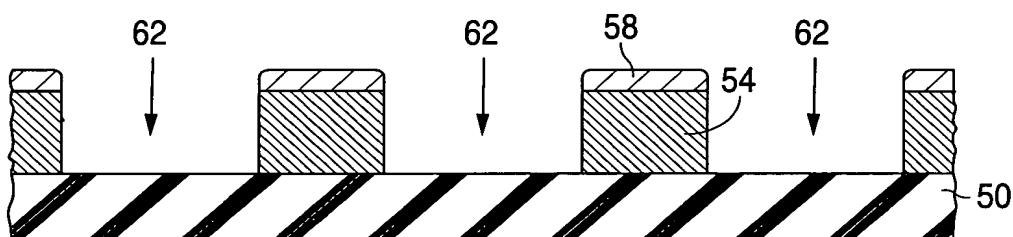




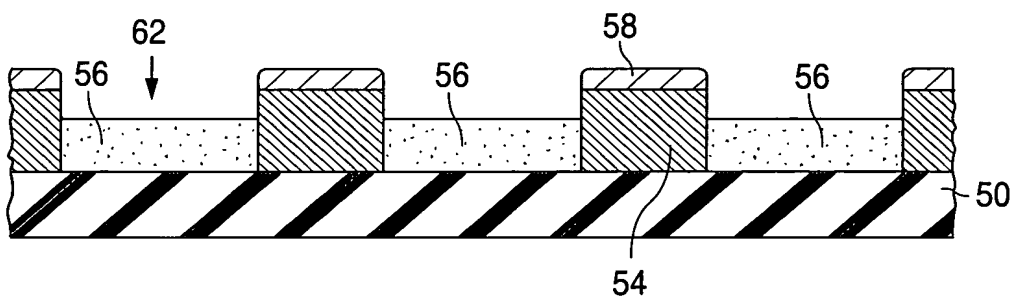
**Fig.
10a**



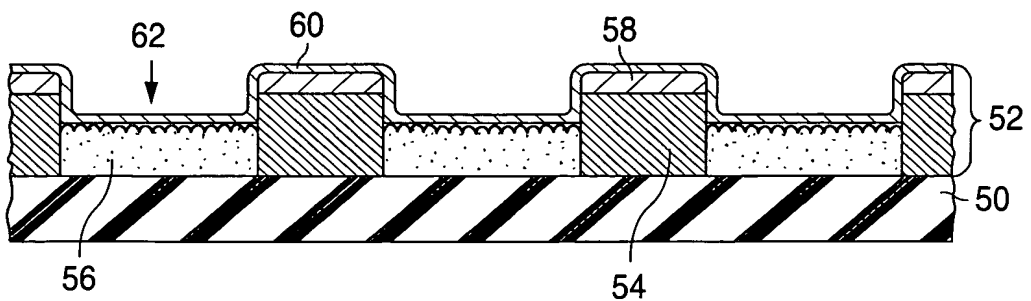
**Fig.
10b**

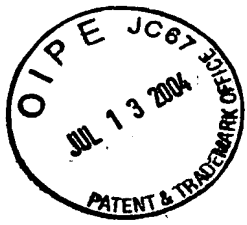


**Fig.
10c**



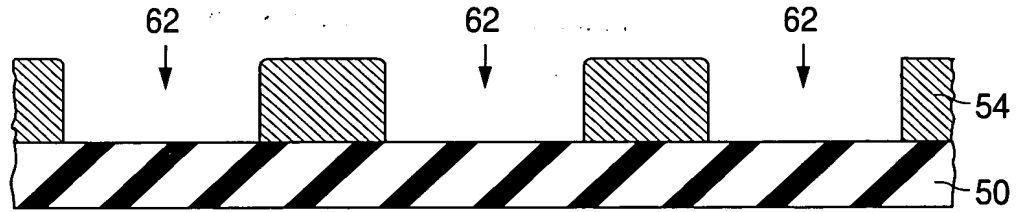
**Fig.
10d**



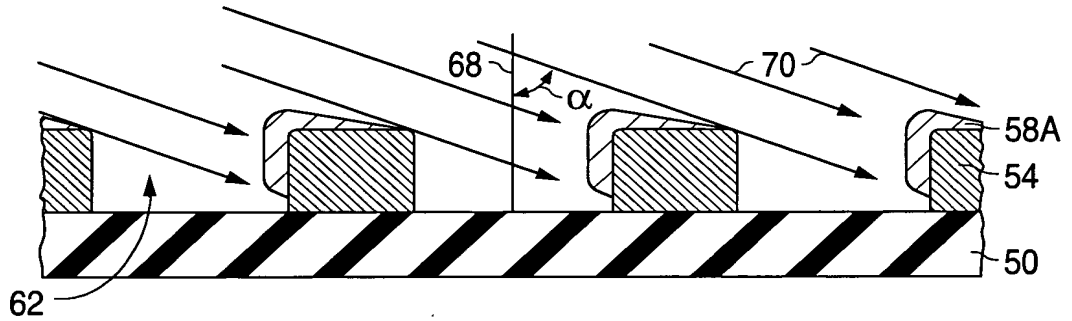


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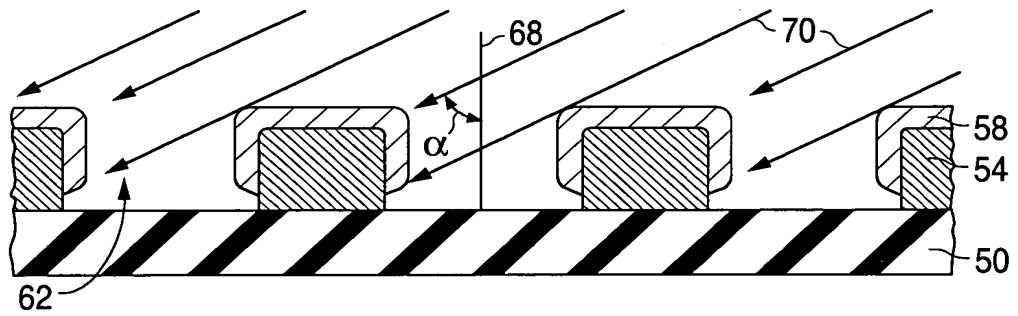
**Fig.
11a**



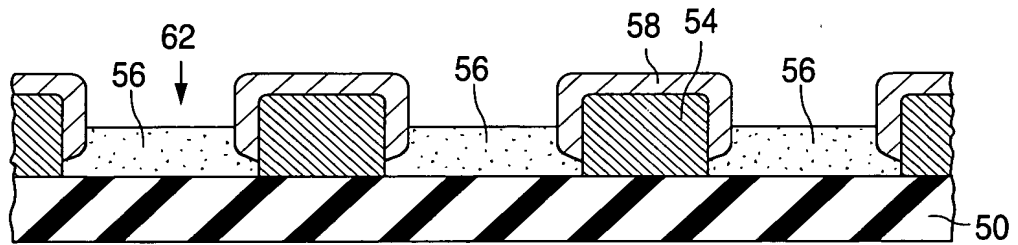
**Fig.
11b**



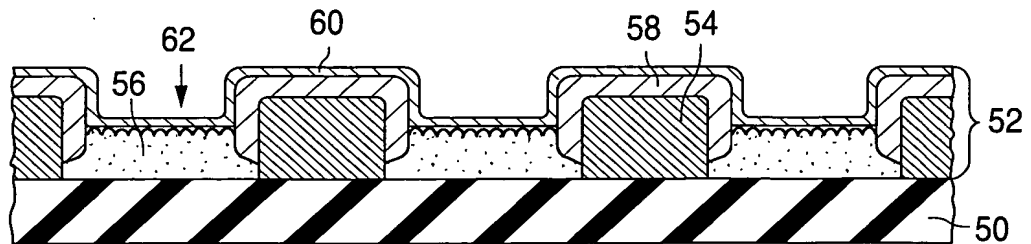
**Fig.
11c**



**Fig.
11d**

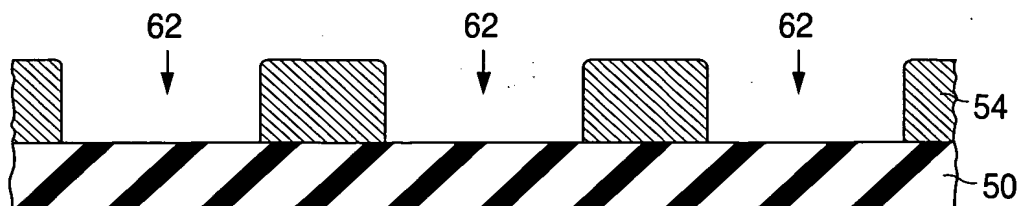


**Fig.
11e**

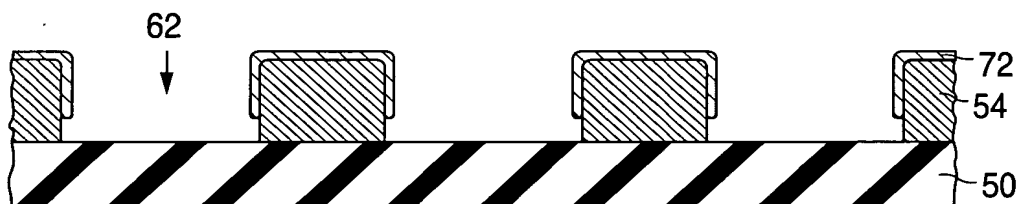


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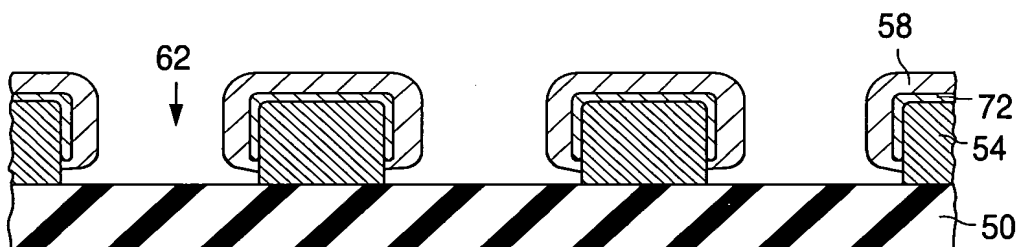
**Fig.
12a**



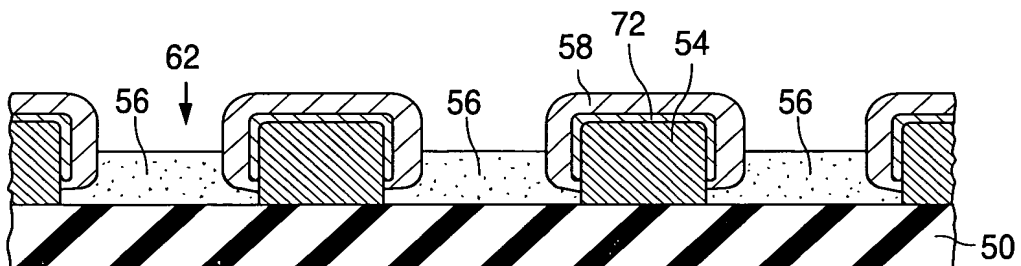
**Fig.
12b**



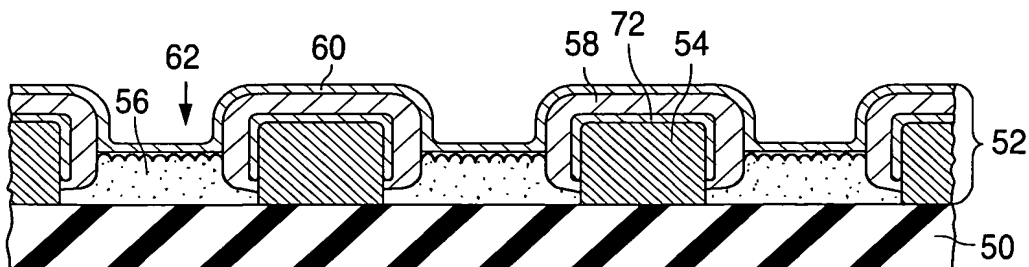
**Fig.
12c**



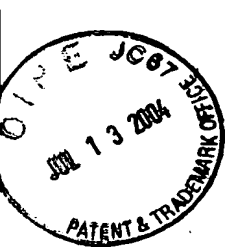
**Fig.
12d**



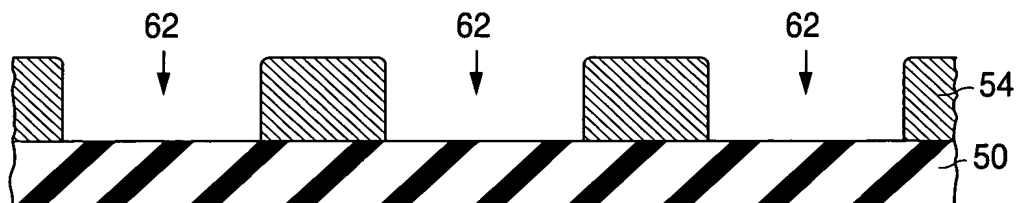
**Fig.
12e**



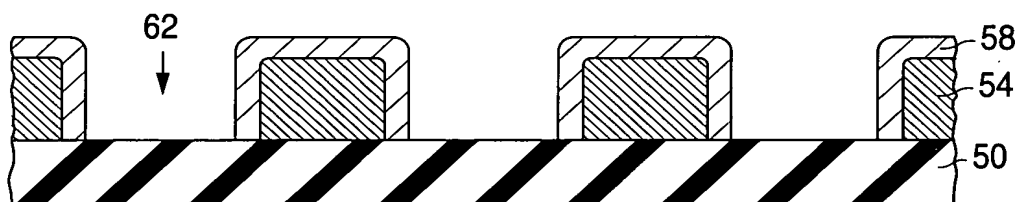
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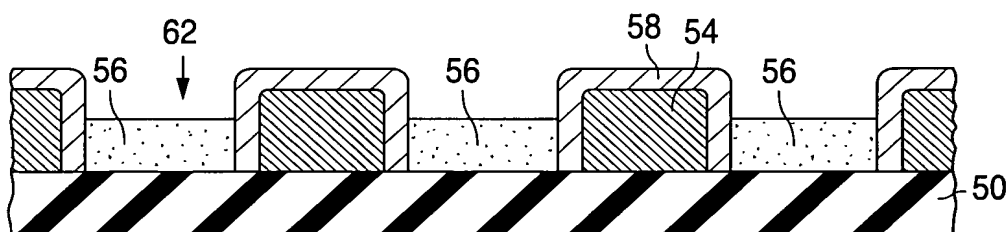
**Fig.
13a**



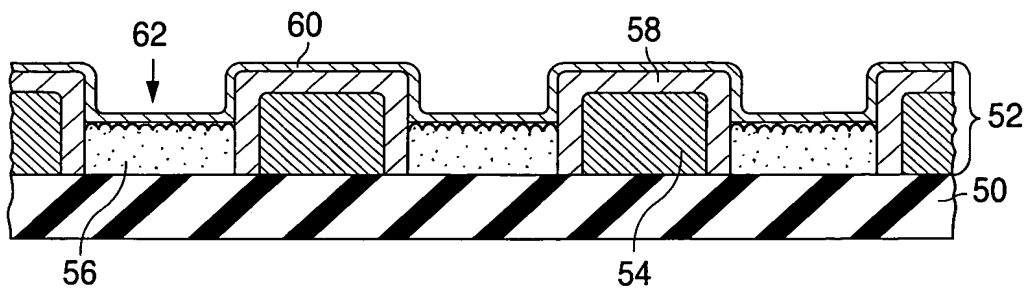
**Fig.
13b**



**Fig.
13c**

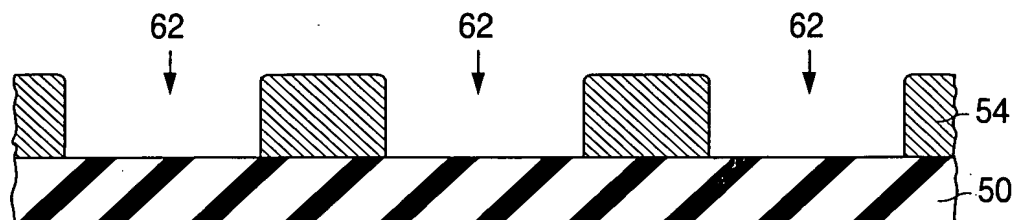


**Fig.
13d**

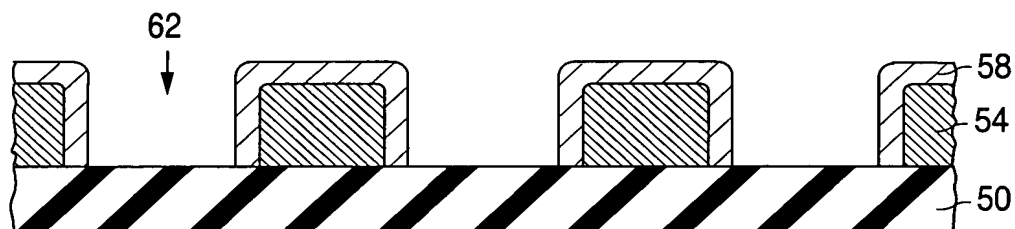


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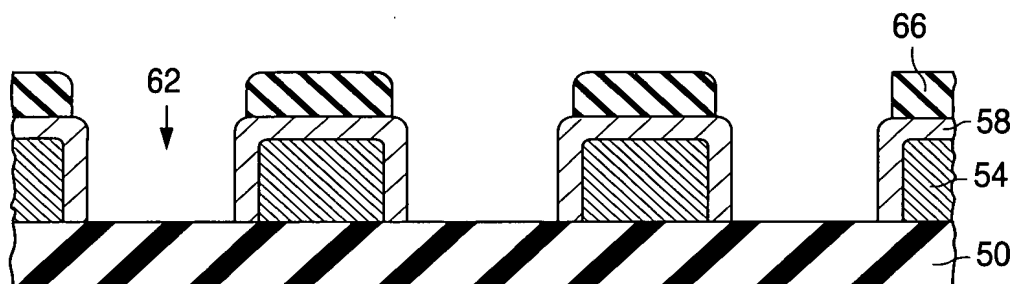
**Fig.
14a**



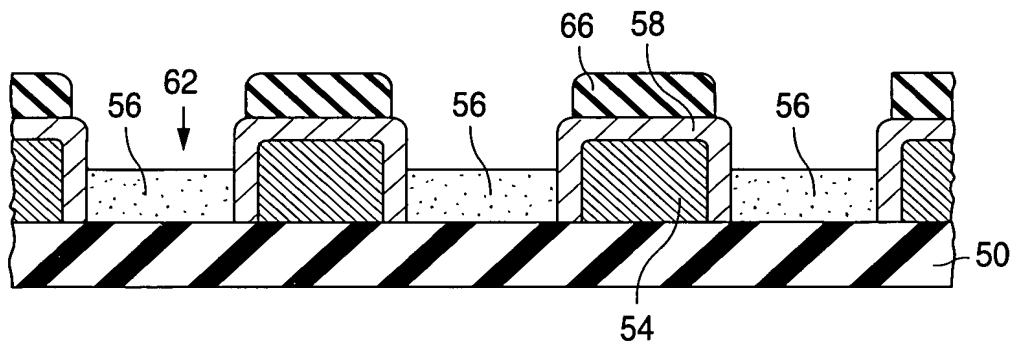
**Fig.
14b**



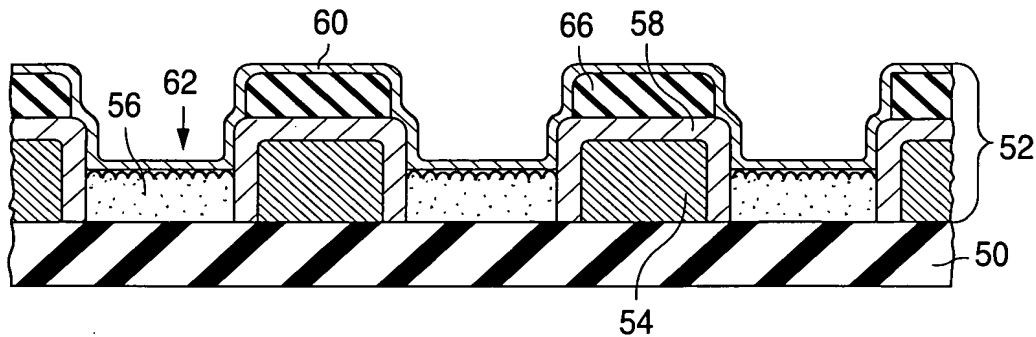
**Fig.
14c**



**Fig.
14d**

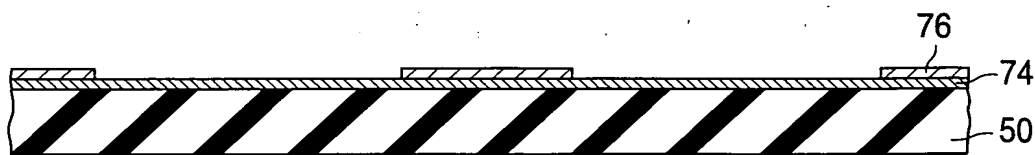
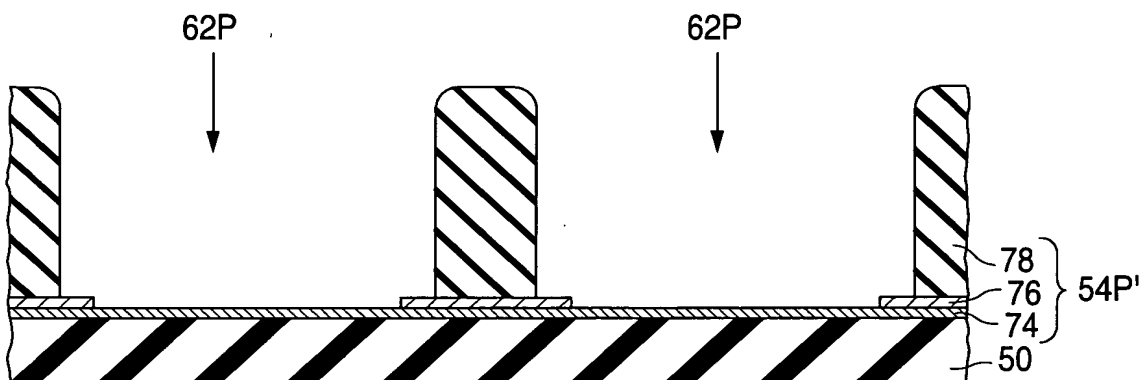
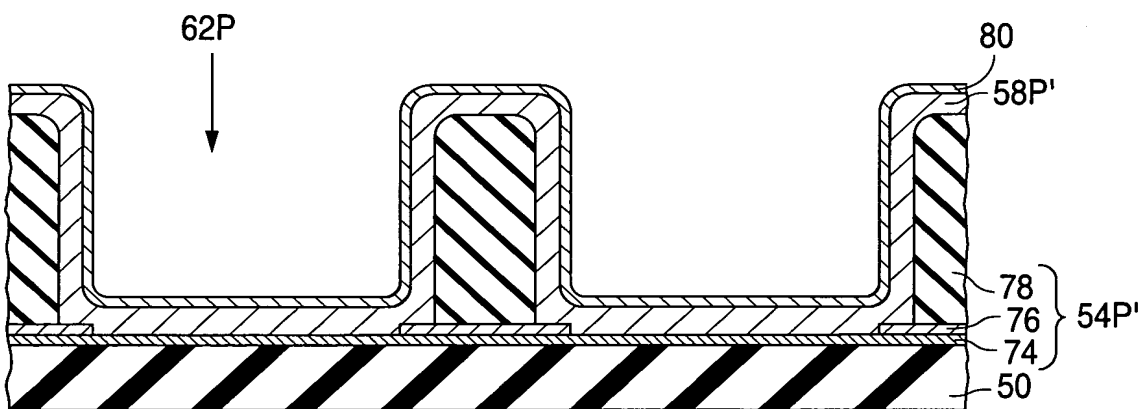
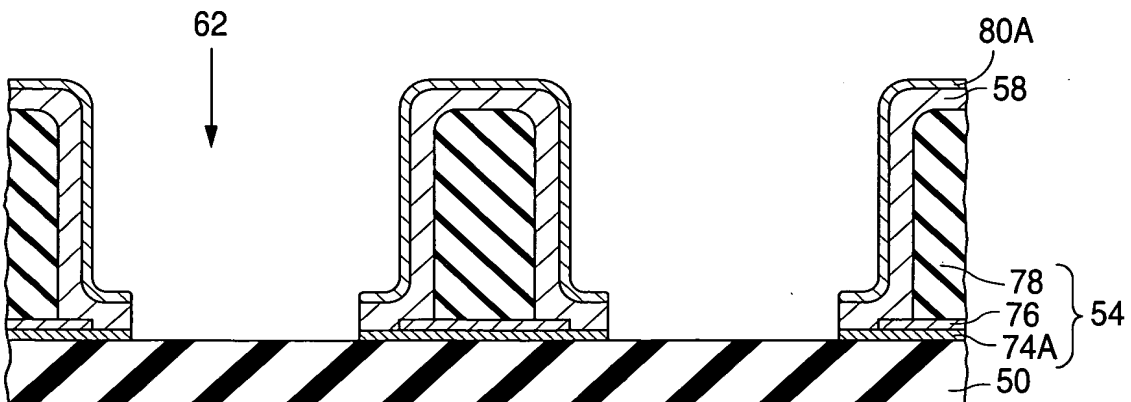


**Fig.
14e**





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**Fig.
15a****Fig.
15b****Fig.
15c****Fig.
15d**

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Fig. 15e

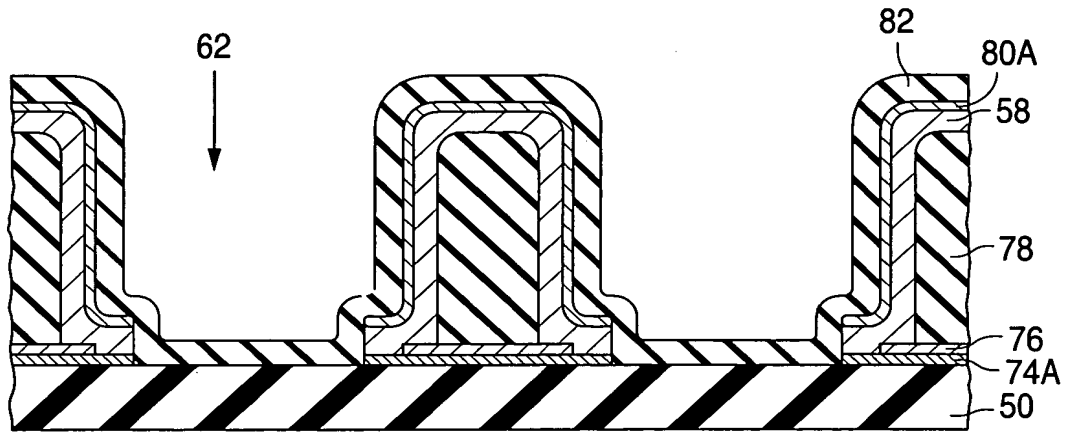


Fig. 15f

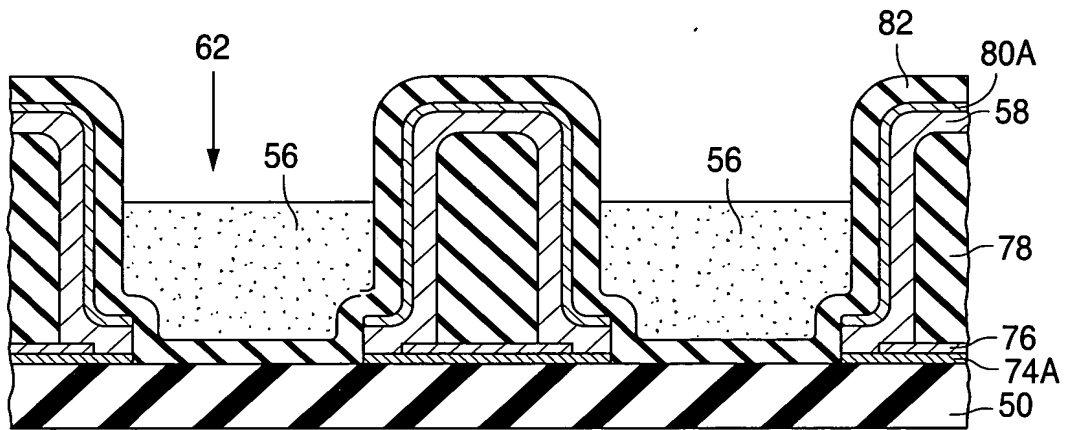
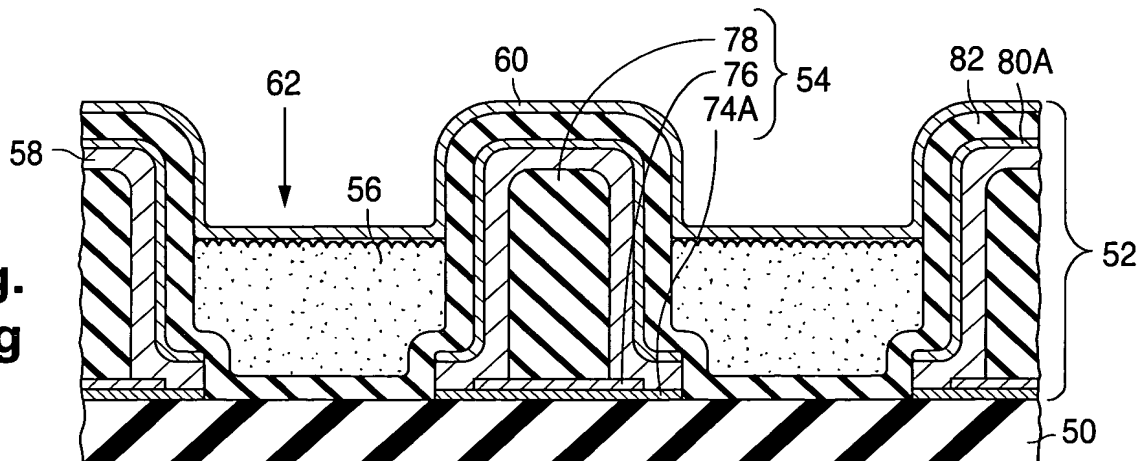


Fig. 15g



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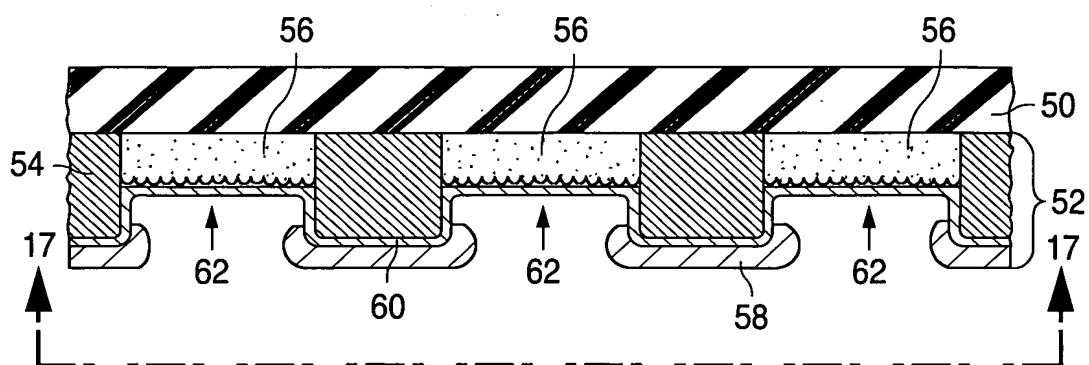


Fig. 16

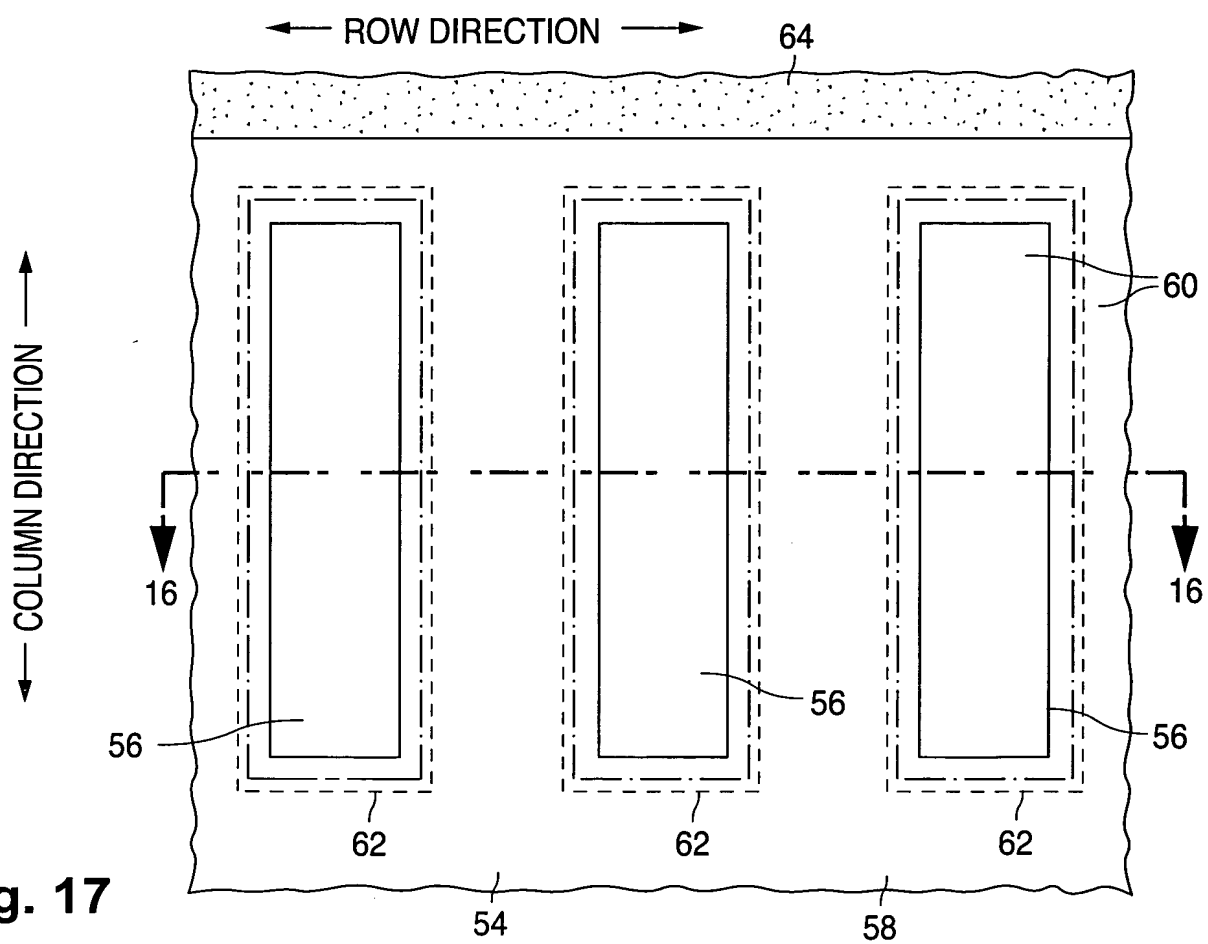
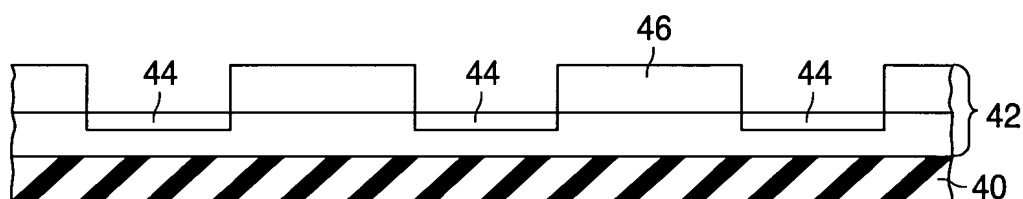
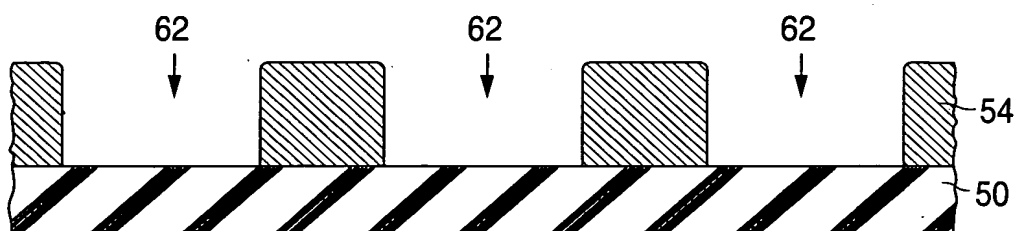


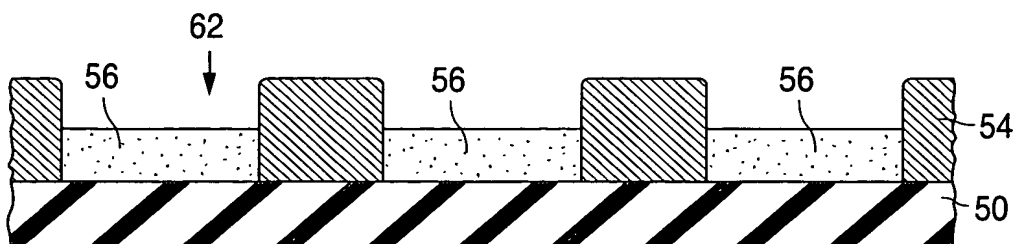
Fig. 17

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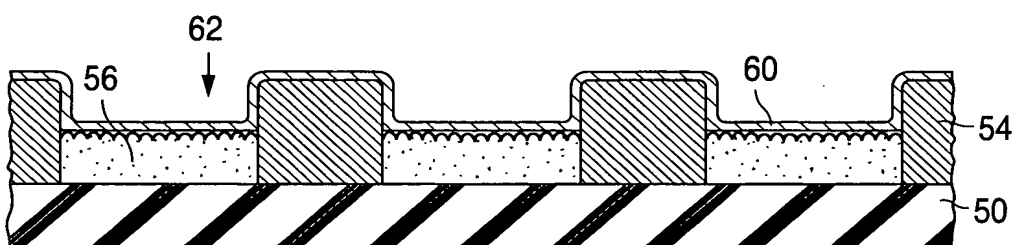
**Fig.
18a**



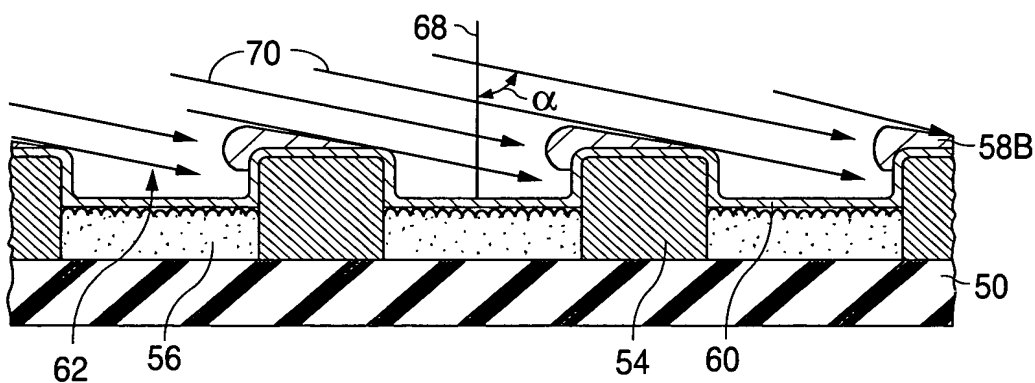
**Fig.
18b**



**Fig.
18c**



**Fig.
18d**



**Fig.
18e**

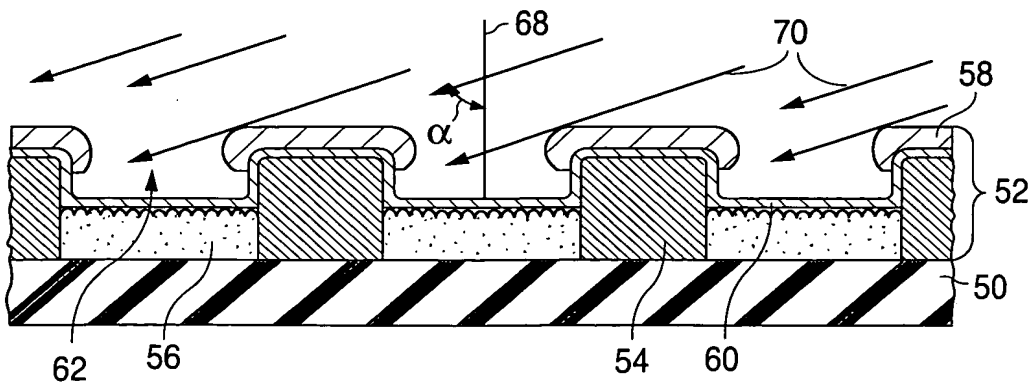


Fig. 19

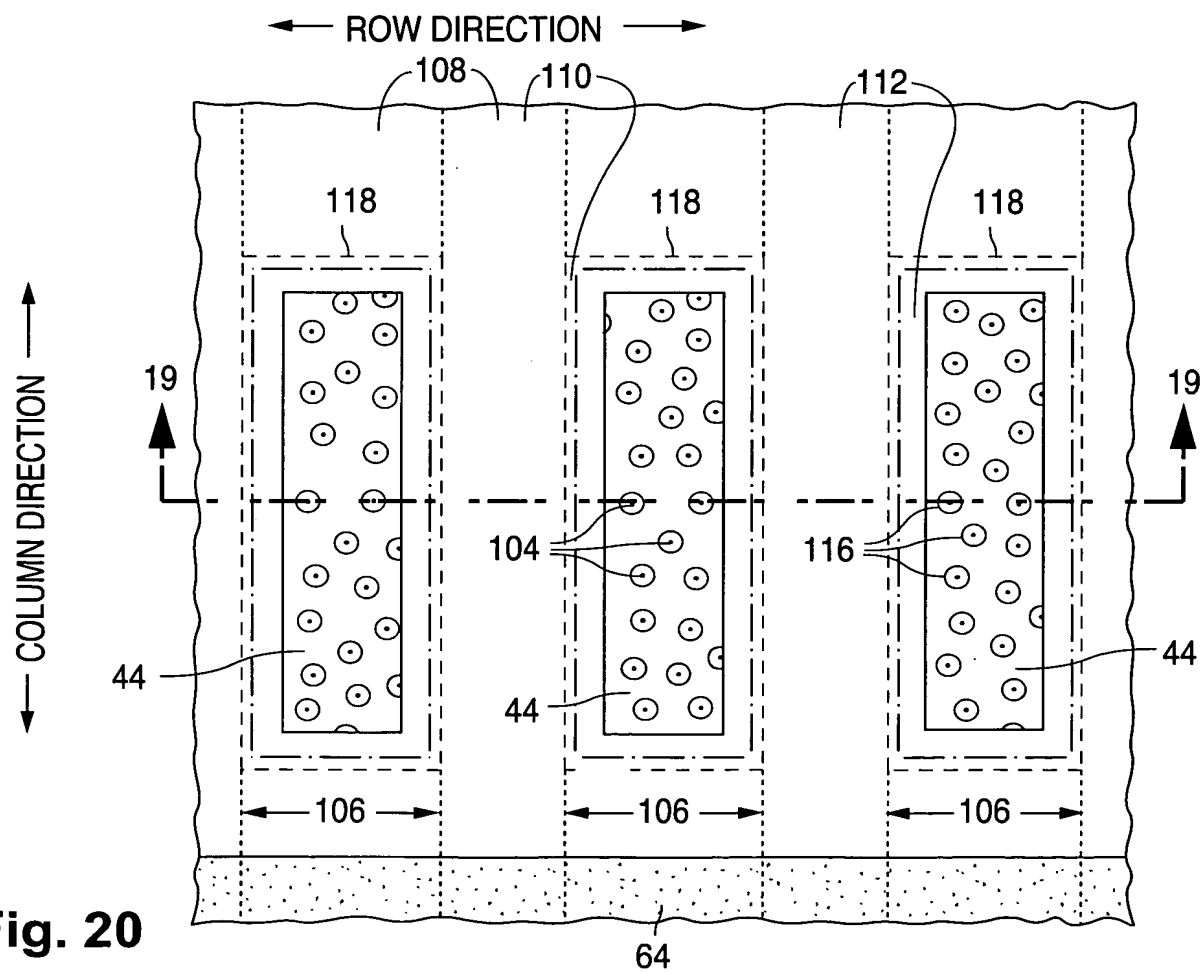
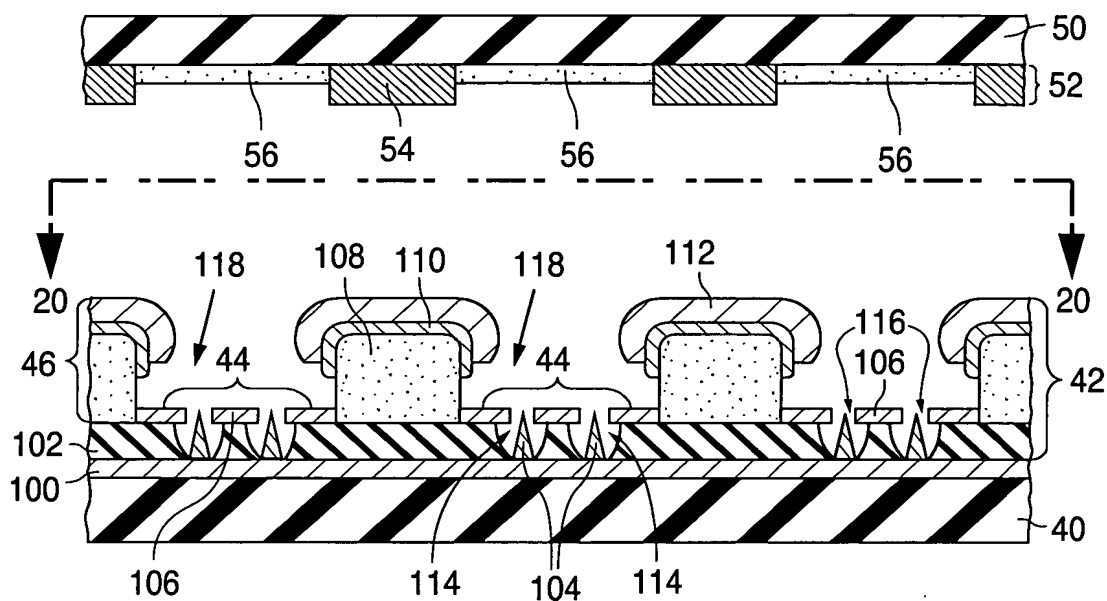


Fig. 20

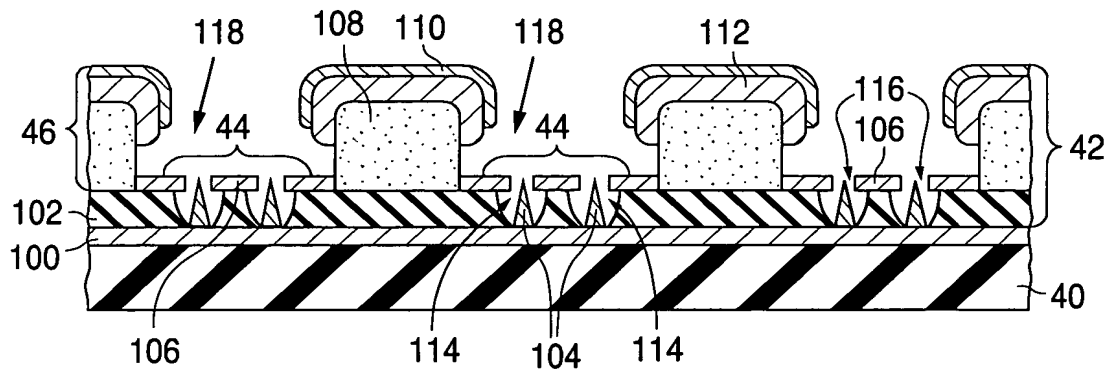


Fig. 21

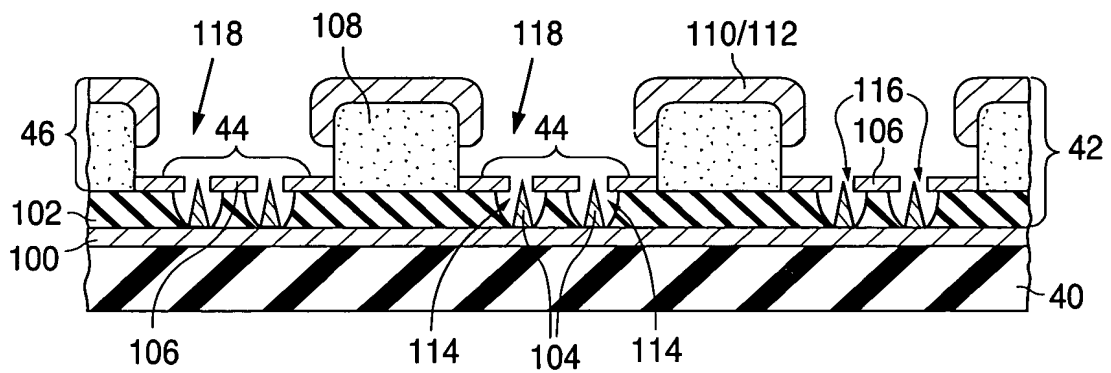


Fig. 22

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Fig. 23a

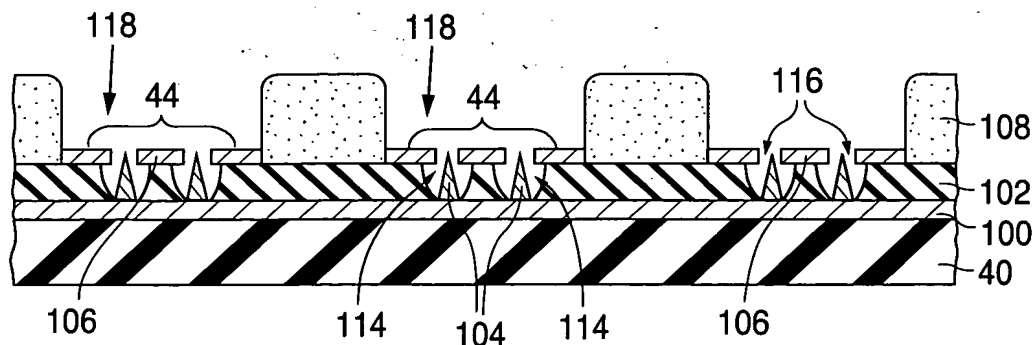


Fig. 23b

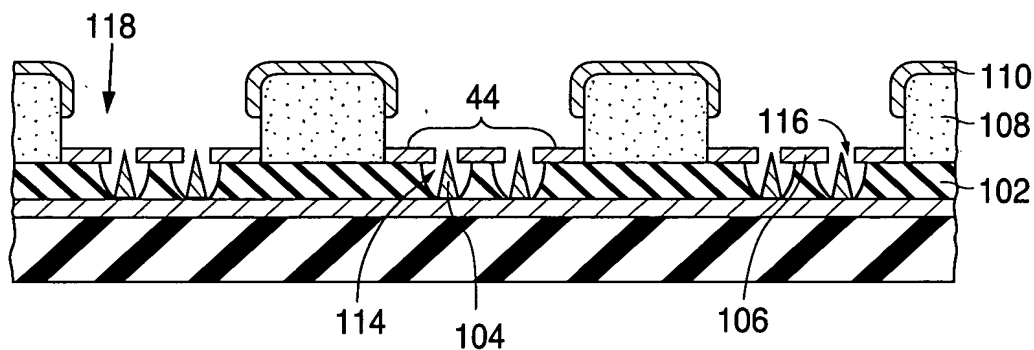


Fig. 23c

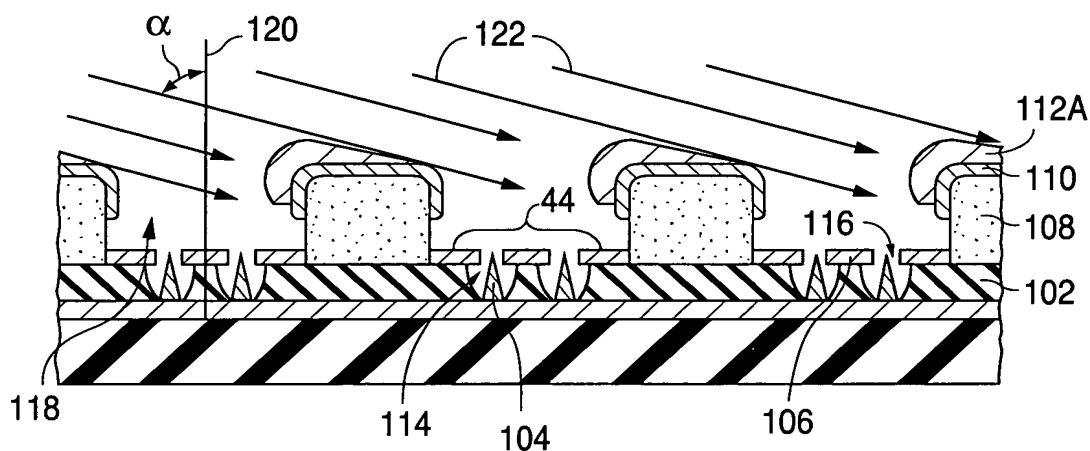
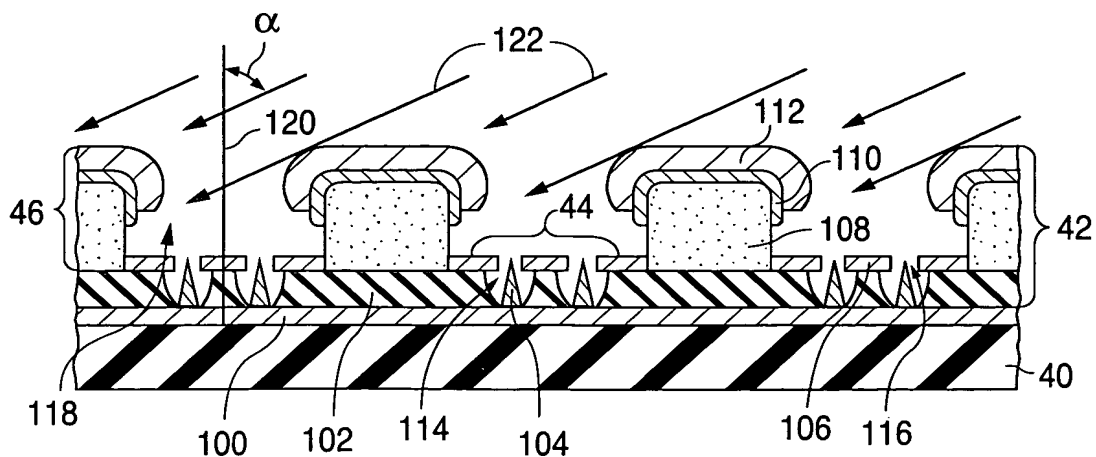


Fig. 23d



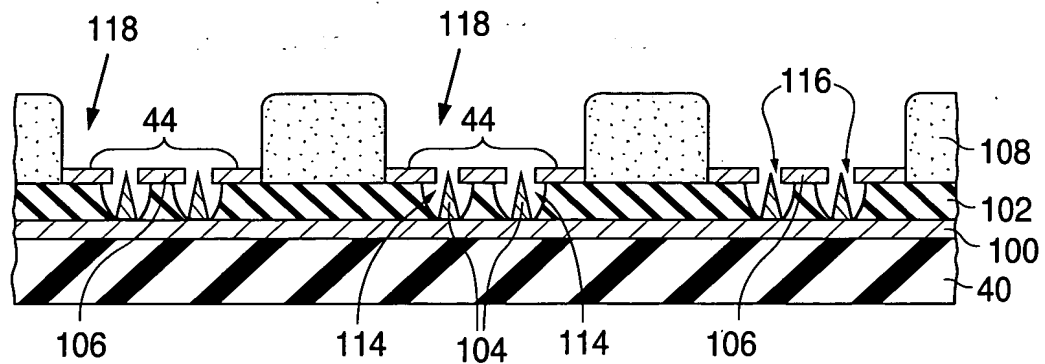
[illegible]

A cross-sectional view of a semiconductor device. A substrate 100 is shown at the bottom. A patterned layer 102 is formed on the substrate, with regions 104, 106, and 114. A top layer 108 is formed on the patterned layer 102. A layer 110 is formed on the top layer 108. A layer 116 is formed on the top layer 108. A layer 118 is formed on the top layer 108. A layer 44 is formed on the top layer 108.

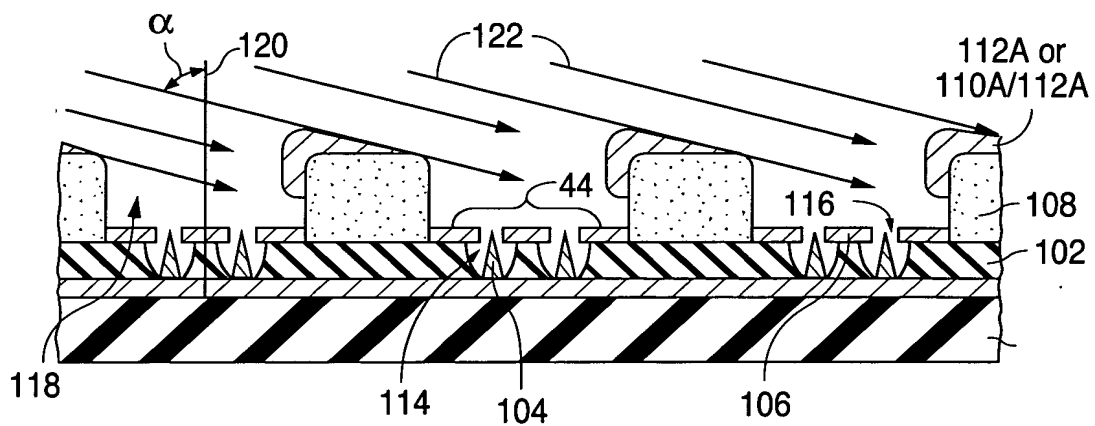
This cross-sectional view shows a substrate with a patterned layer 40. The patterned layer 40 has a series of rectangular blocks 100, 102, 104, and 106. Above these blocks is a layer 42. The layer 42 has a series of rectangular blocks 110, 112, and 116. The blocks 110, 112, and 116 are connected by a material 108. The blocks 110, 112, and 116 are also connected to the blocks 100, 102, 104, and 106 by a material 114. The blocks 110, 112, and 116 are also connected to the blocks 100, 102, 104, and 106 by a material 118. The blocks 110, 112, and 116 are also connected to the blocks 100, 102, 104, and 106 by a material 116.

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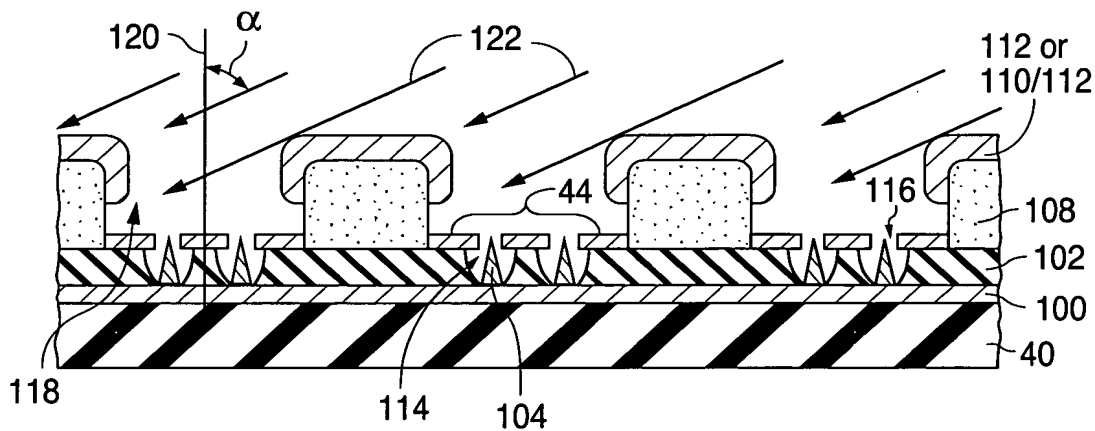
**Fig.
25a**



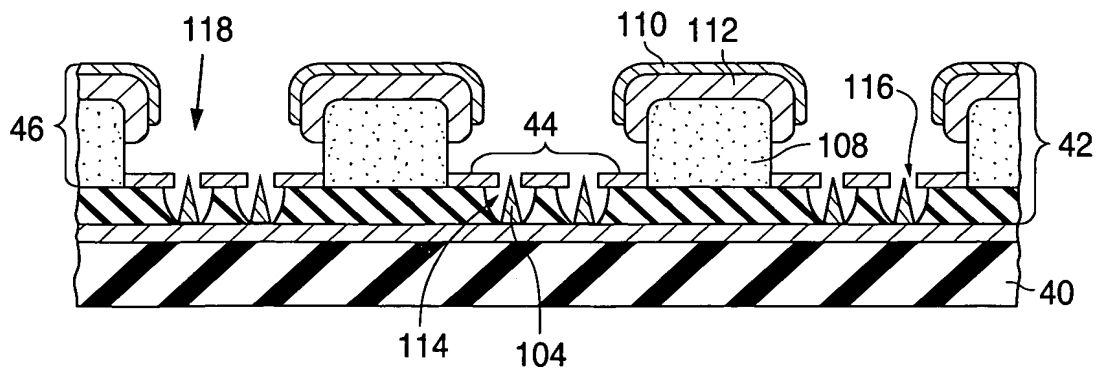
**Fig.
25b**



**Fig.
25c**



**Fig.
25d**



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Fig. 26

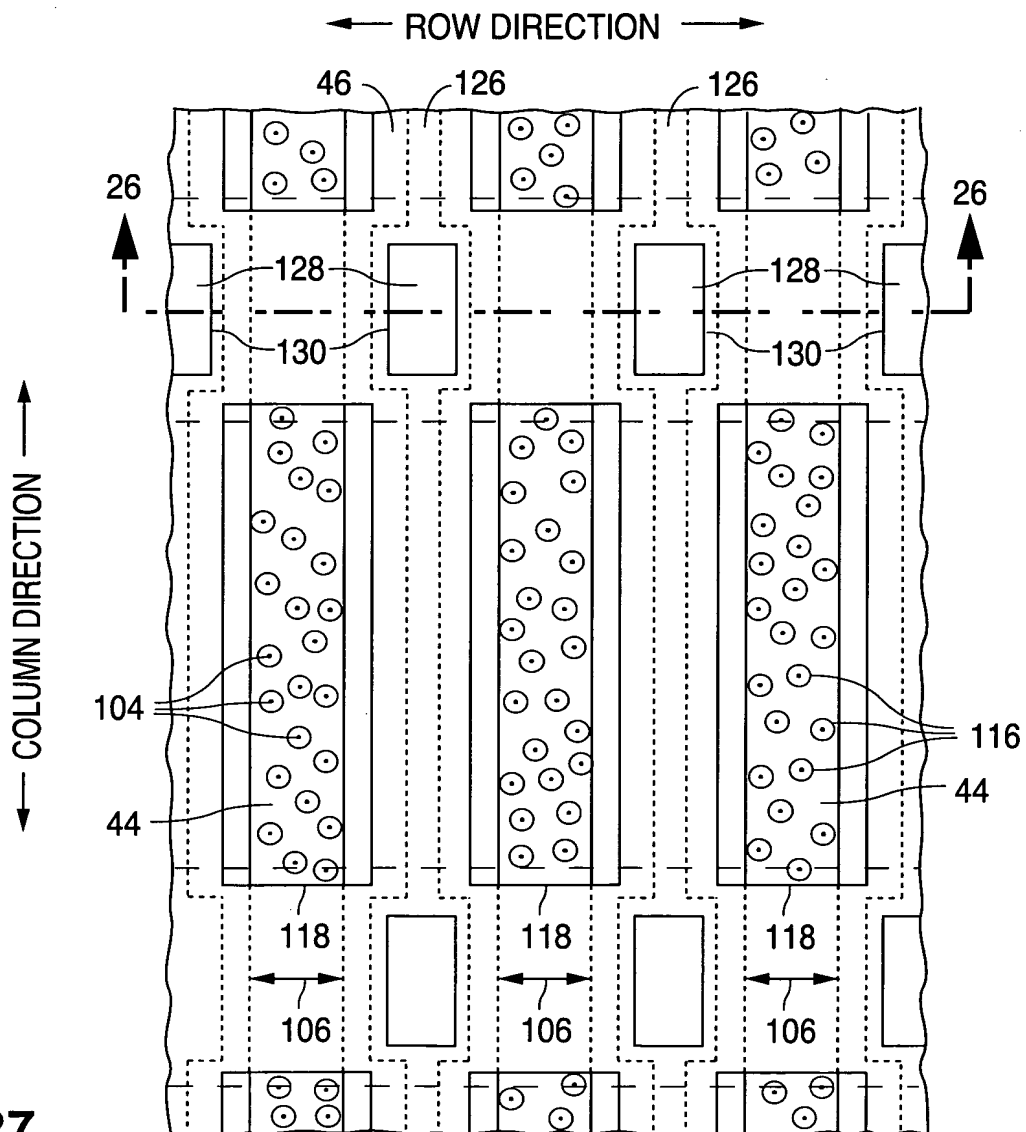
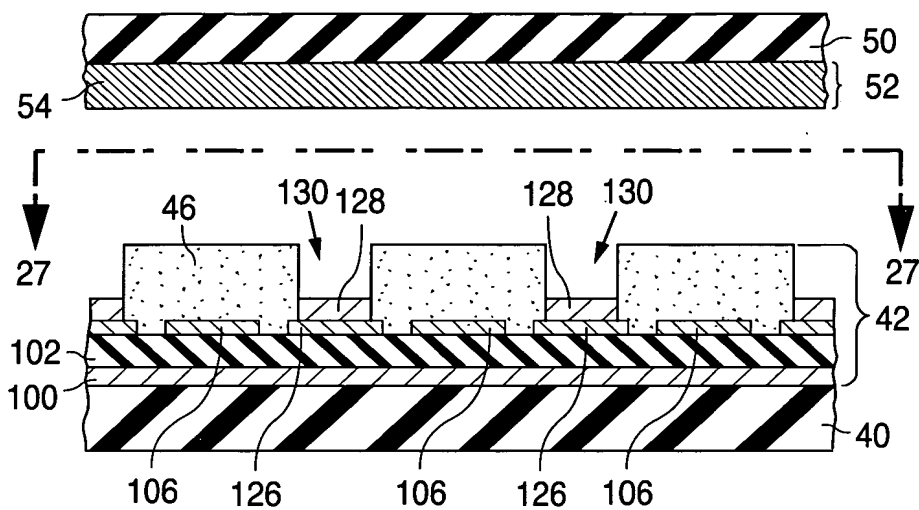
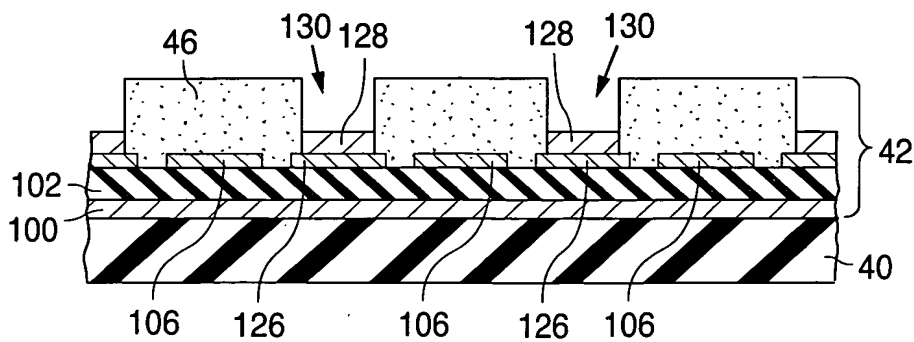
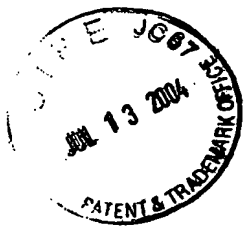


Fig. 27





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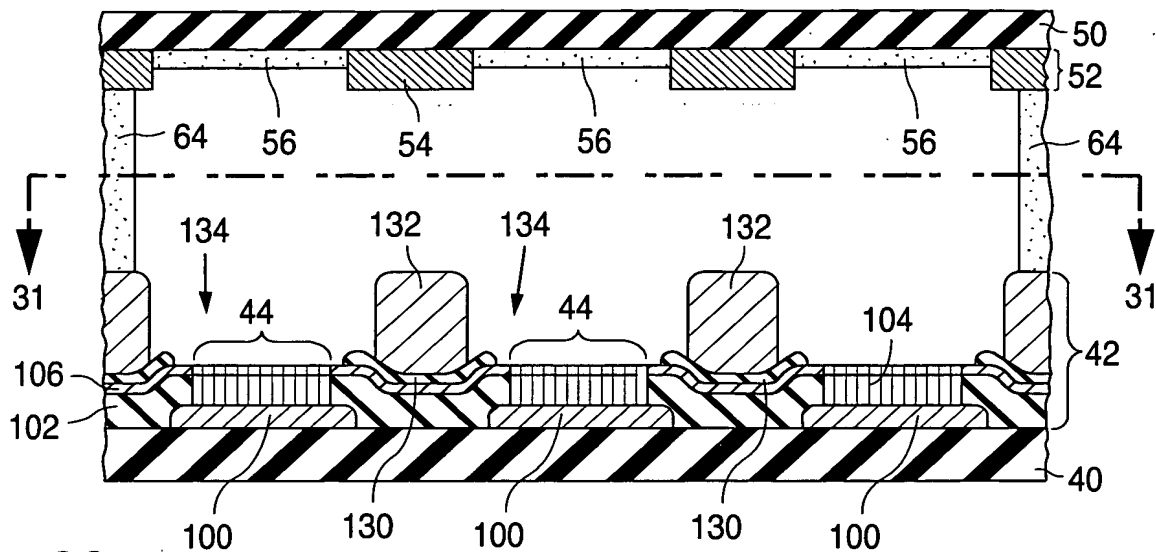


Fig. 30

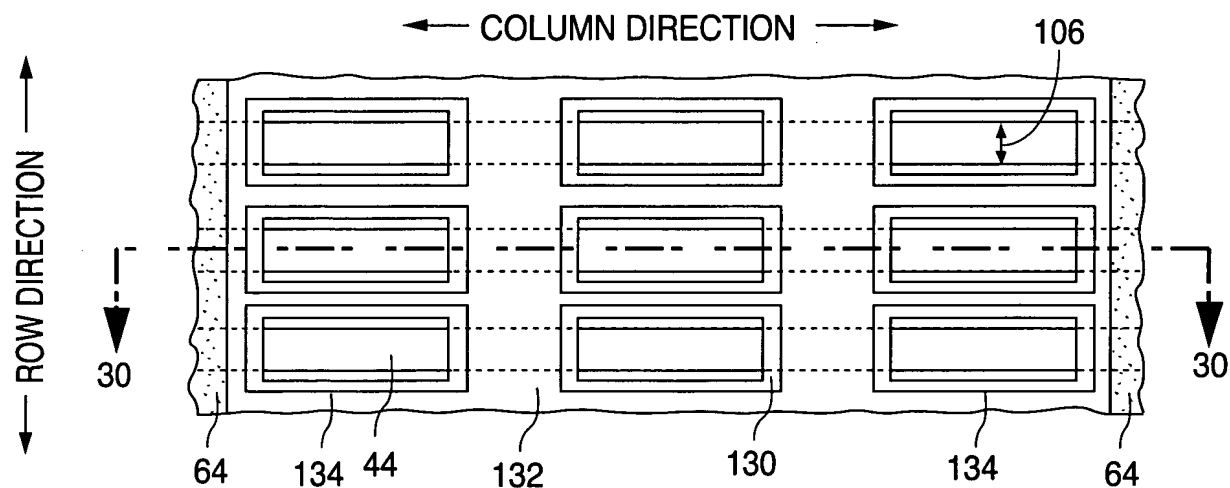


Fig. 31

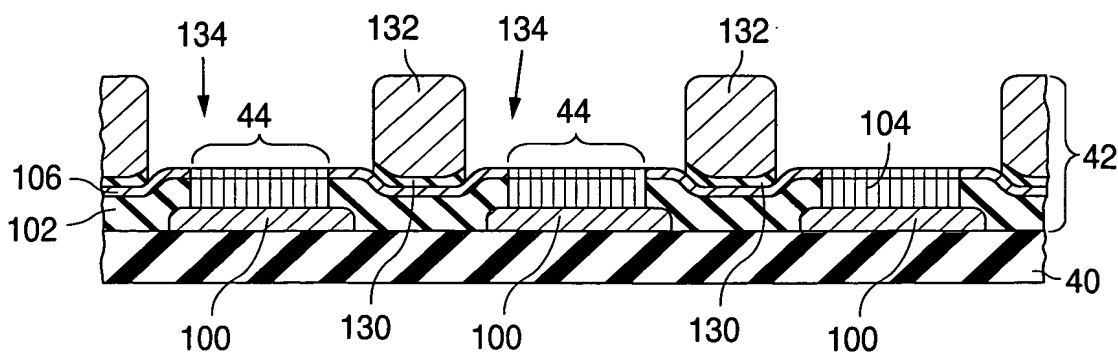
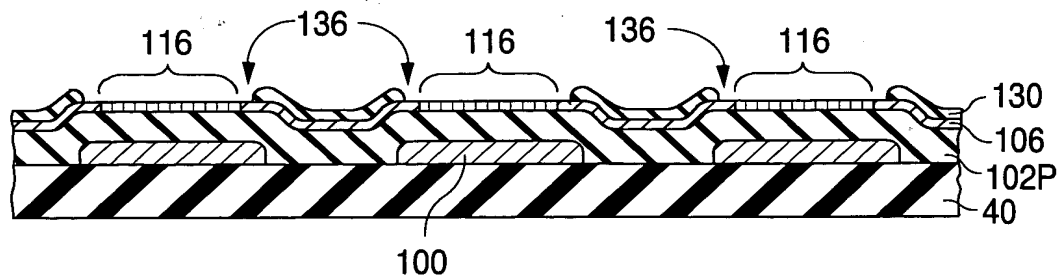
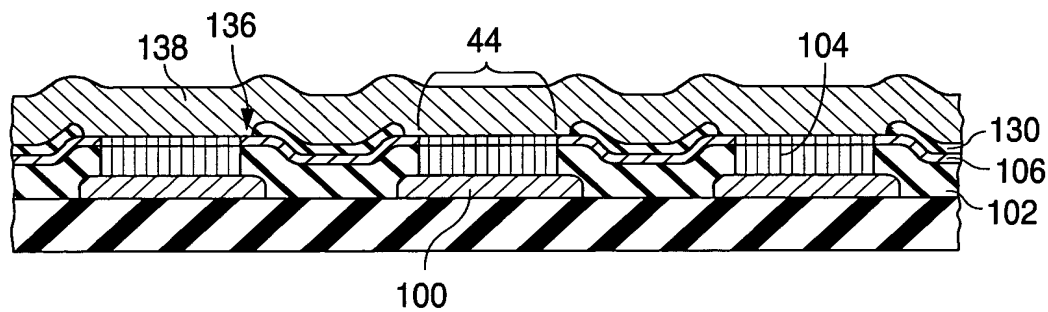


Fig. 32

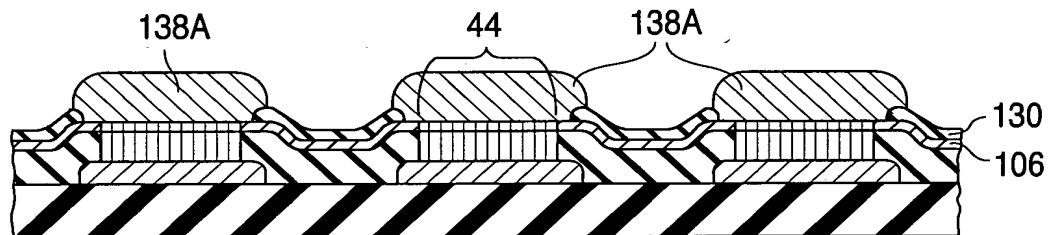
**Fig.
33a**



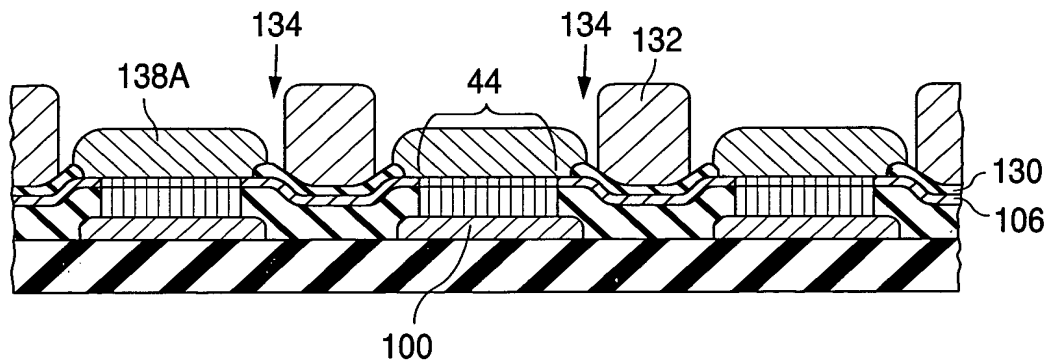
**Fig.
33b**



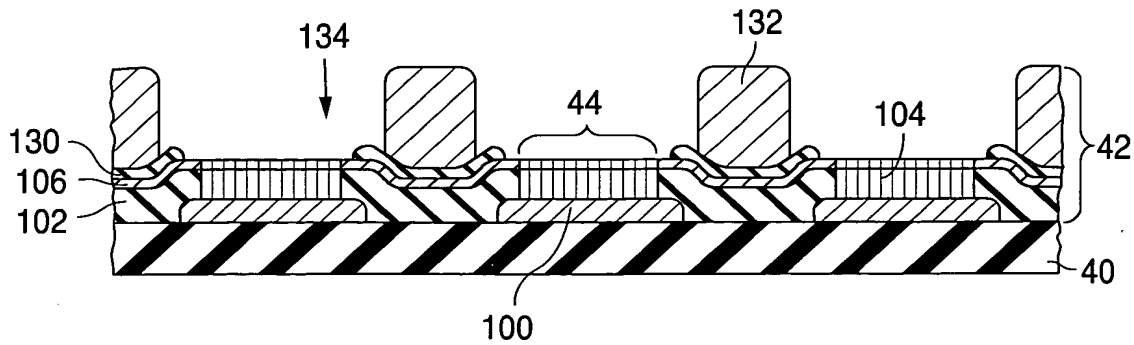
**Fig.
33c**



**Fig.
33d**



**Fig.
33e**



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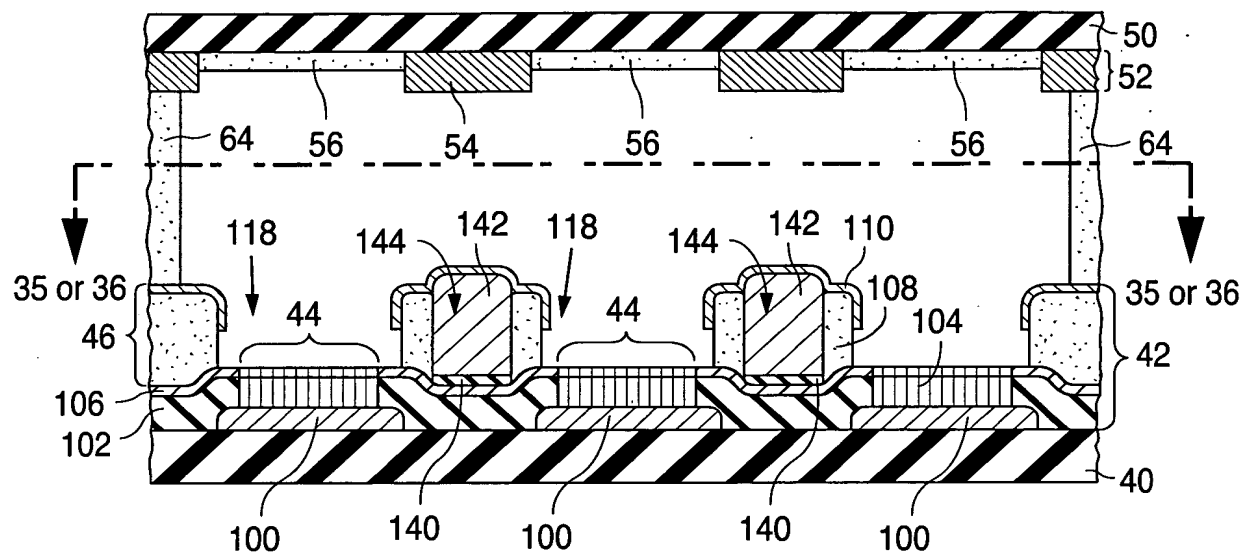


Fig. 34

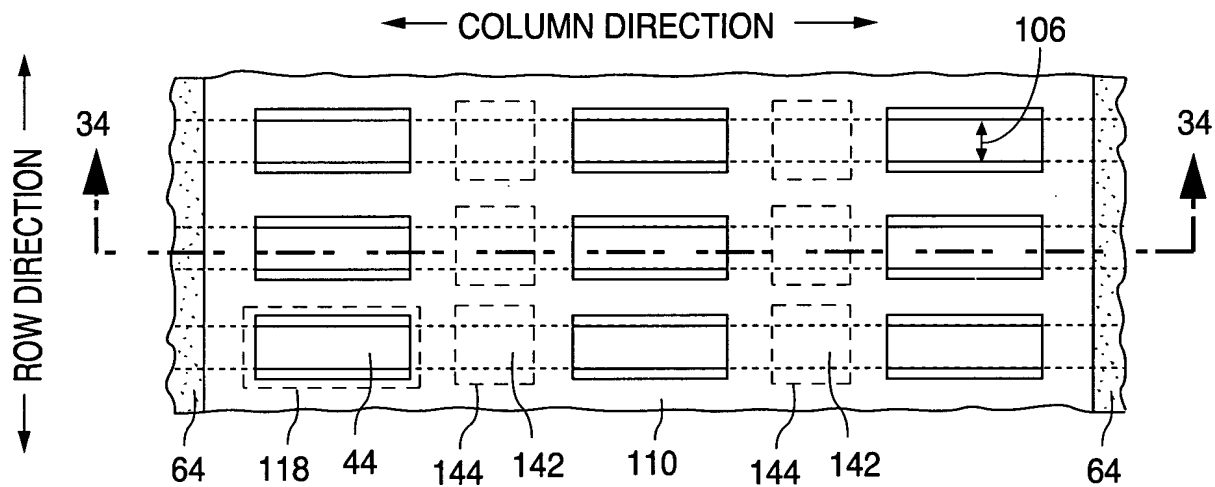


Fig. 35

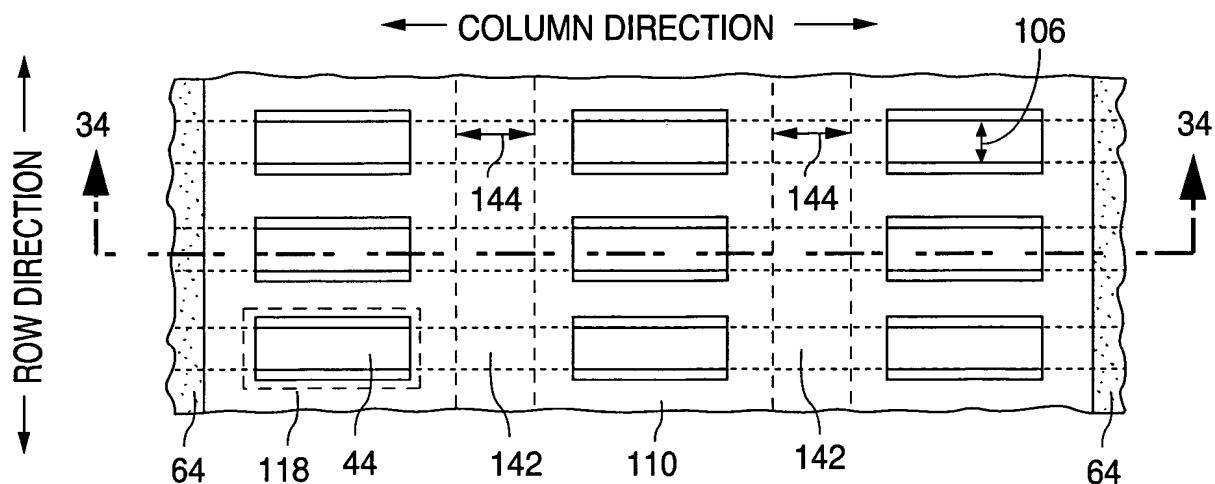


Fig. 36

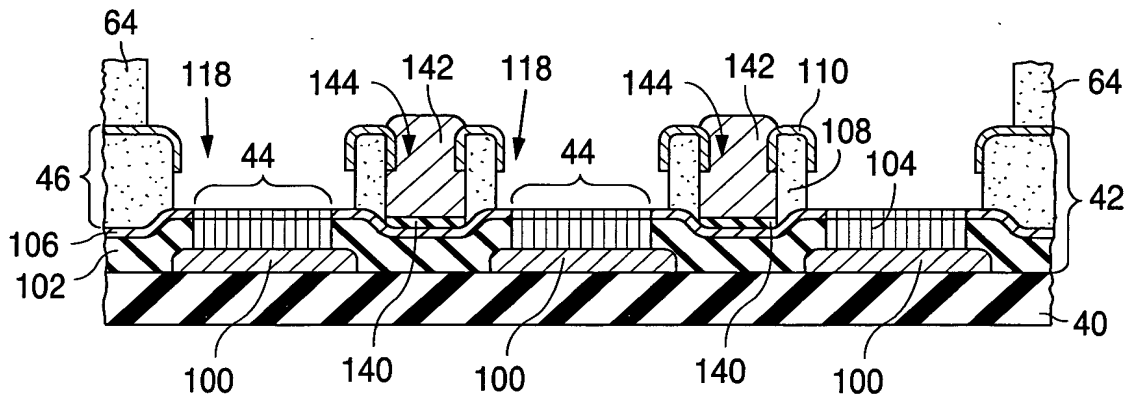


Fig. 37

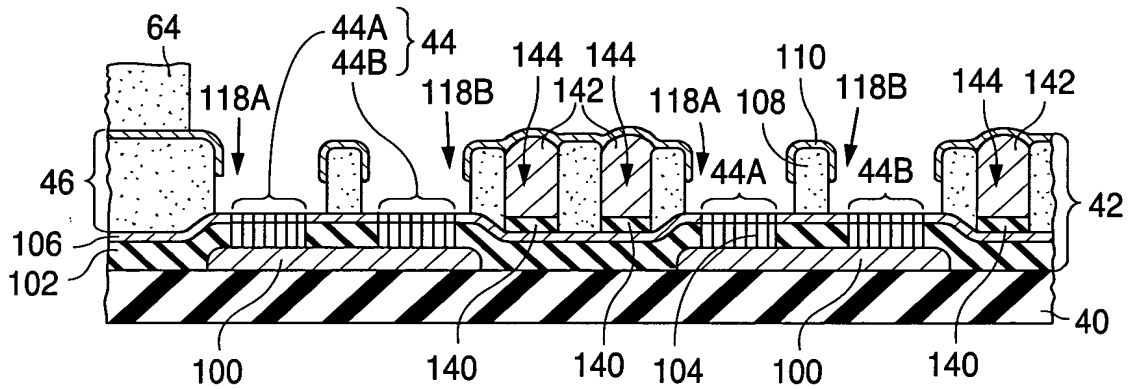


Fig. 38

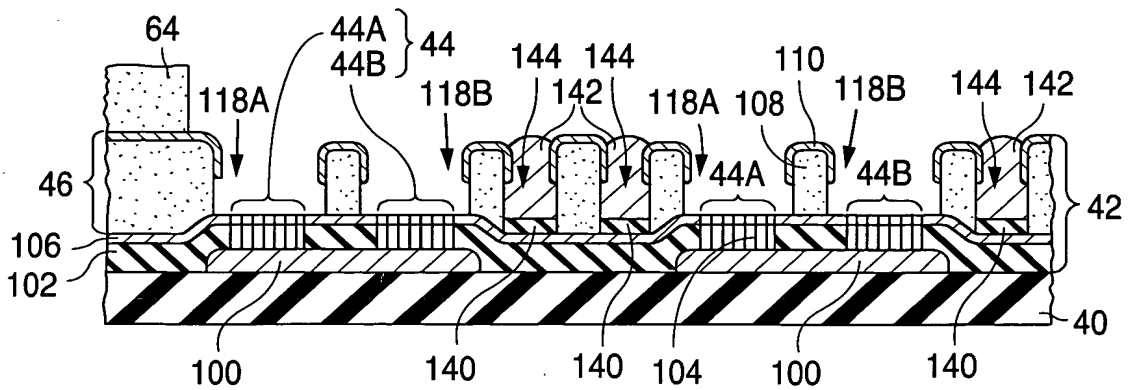
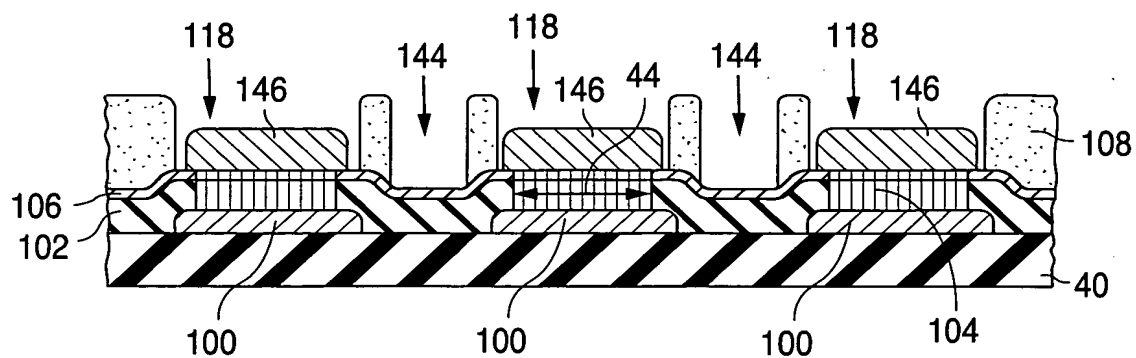
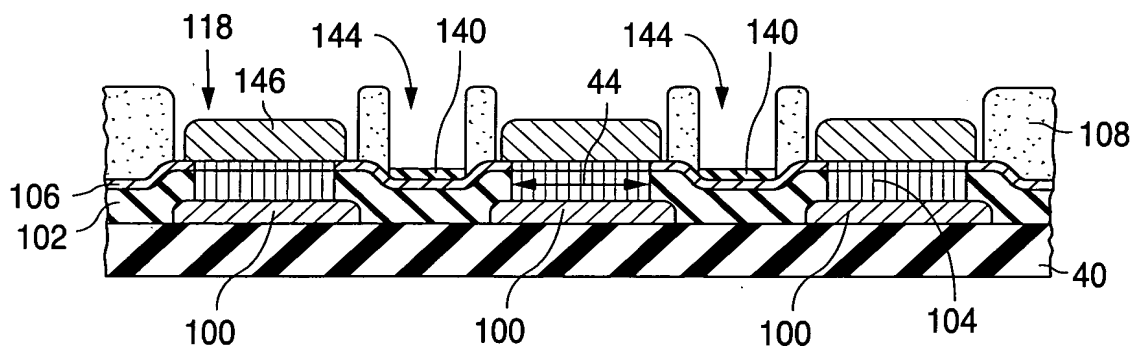


Fig. 39

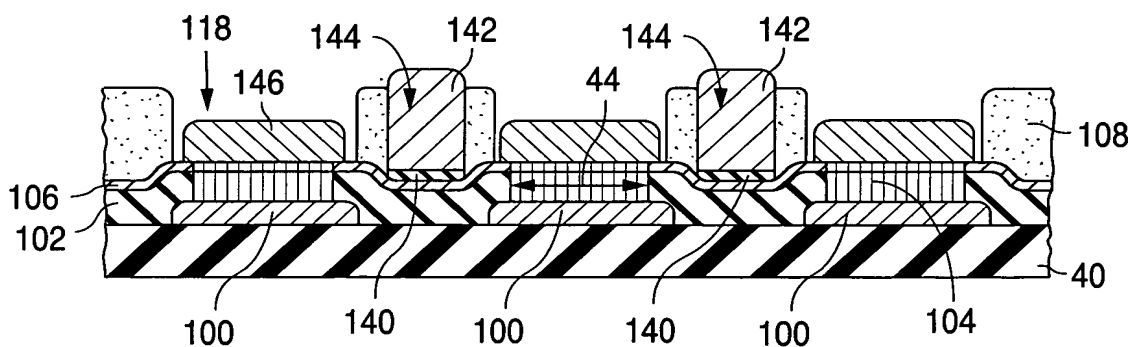
**Fig.
40a**



**Fig.
40b**



**Fig.
40c**



**Fig.
40d**

